

V_{RRM} = 1200 V
 $I_F (T_C=165^{\circ}C)$ = 10 A**
 Q_C = 64 nC**

Features

- Extremely low reverse current
- No reverse recovery current
- Temperature independent switching
- Positive temperature coefficient on V_F
- Excellent surge current capability
- Low capacitive charge

Benefits

- Essentially no switching losses
- System efficiency improvement over Si diodes
- Increased power density
- Enabling higher switching frequency
- Reduction of heat sink requirements
- System cost savings due to smaller magnetics
- Reduced EMI

Applications

- Switch mode power supplies (SMPS)
- Uninterruptible power supplies
- Motor drivers
- Power factor correction

Package Pin Definitions

- Pin1- Anode
- Pin2- Cathode
- Pin3- Anode

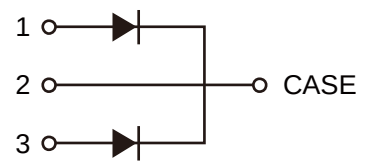
Package Parameters

Part Number	Marking	Package
B1D10120HC	B1D10120HC	TO-247-3

* Per Leg, ** Per Device

TO-247-3

CASE



Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Value	Unit
V_{RRM}	Repetitive peak reverse voltage		1200	V
V_{RSM}	Non-repetitive peak reverse voltage		1200	V
I_F	Continuous forward current	$T_c=25^\circ\text{C}$ $T_c=165^\circ\text{C}$	30*/60** 5*/10**	A
I_{FSM}	Non-repetitive forward surge current	$T_c=25^\circ\text{C}$, $t_p=10\text{ms}$, Half Sine Wave	60*	A
$\int i^2 dt$	i^2t value	$T_c=25^\circ\text{C}$, $t_p=10\text{ms}$	18*	A ² S
P_{tot}	Power dissipation	$T_c=25^\circ\text{C}$ $T_c=110^\circ\text{C}$	208* 90*	W
T_j	Operating junction temperature		-55~175	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~175	$^\circ\text{C}$
	TO-247 mounting torque	M3 Screw	0.7	Nm

* Per Leg, ** Per Device

Thermal Characteristics

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
$R_{th(jc)}$	Thermal resistance from junction to case		1.43* 0.72**		K/W

* Per Leg, ** Per Device

Electrical Characteristics (Per Leg)
Static Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
V_{DC}	DC blocking voltage	$T_j=25^{\circ}\text{C}$	1200			V
V_F	Diode forward voltage	$I_F=5\text{A } T_j=25^{\circ}\text{C}$ $I_F=5\text{A } T_j=175^{\circ}\text{C}$		1.40 1.78	1.60 2.20	V
I_R	Reverse current	$V_R=1200\text{V } T_j=25^{\circ}\text{C}$ $V_R=1200\text{V } T_j=175^{\circ}\text{C}$		2 10	90 300	μA

AC Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
Q_C	Total capacitive charge	$V_R=800\text{V } T_j=25^{\circ}\text{C}$ $Q_C = \int_0^{V_R} C(V) dV$		32		nC
C	Total capacitance	$V_R=1\text{V } f=1\text{MHz}$ $V_R=400\text{V } f=1\text{MHz}$ $V_R=800\text{V } f=1\text{MHz}$		352 31 23		pF
E_C	Capacitance stored energy	$V_R=800\text{V}$		16		μJ

Typical Performance (Per Leg)

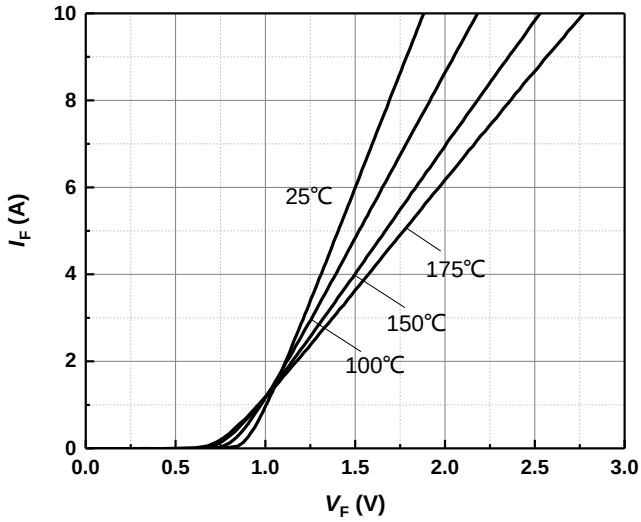


Figure 1. Typical forward characteristics

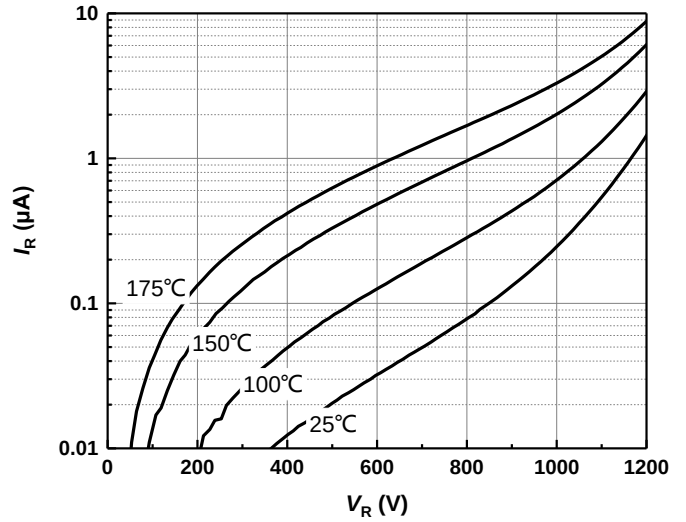


Figure 2. Typical reverse current as function of reverse voltage

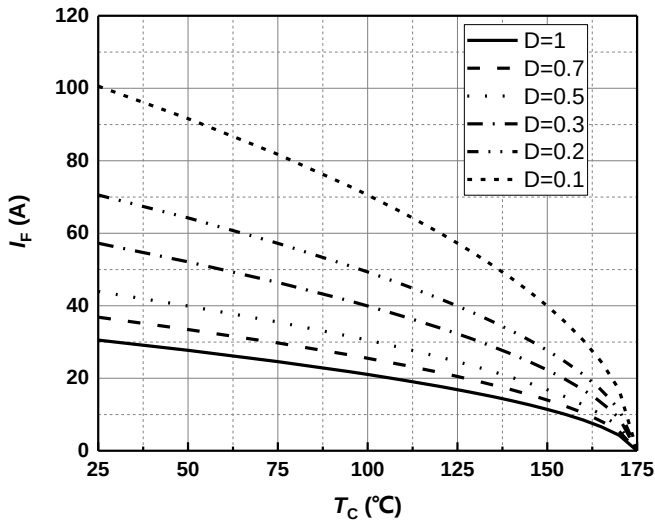


Figure 3. Diode forward current as function of temperature, D=duty cycle

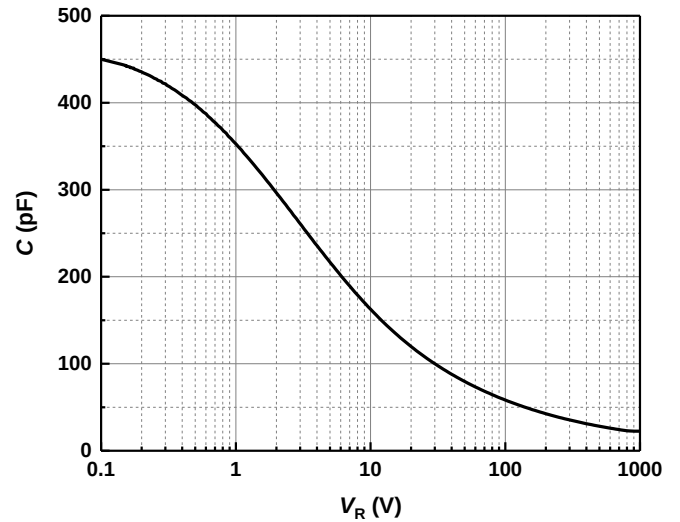


Figure 4. Typical capacitance as function of reverse voltage, $C=f(V_R)$; $T_J=25^\circ\text{C}$; $f=1\text{ MHz}$

Typical Performance

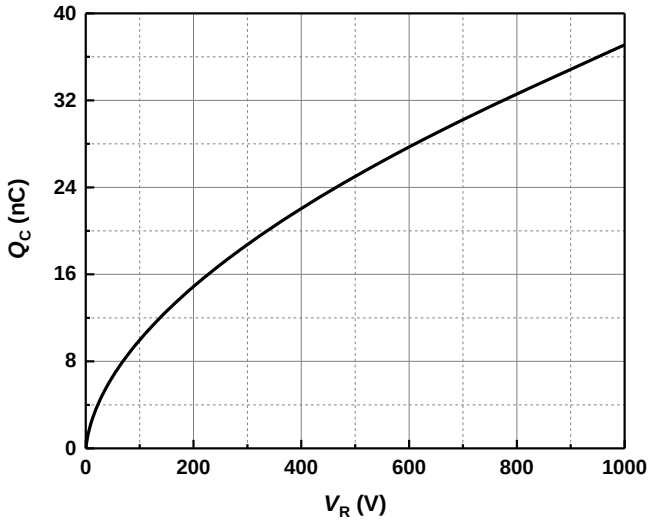


Figure 5. Typical reverse charge as function of reverse voltage

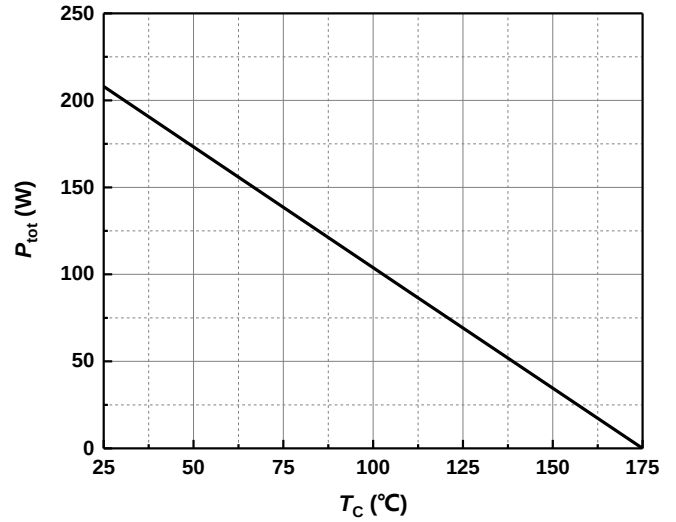


Figure 6. Power dissipation as function of case temperature

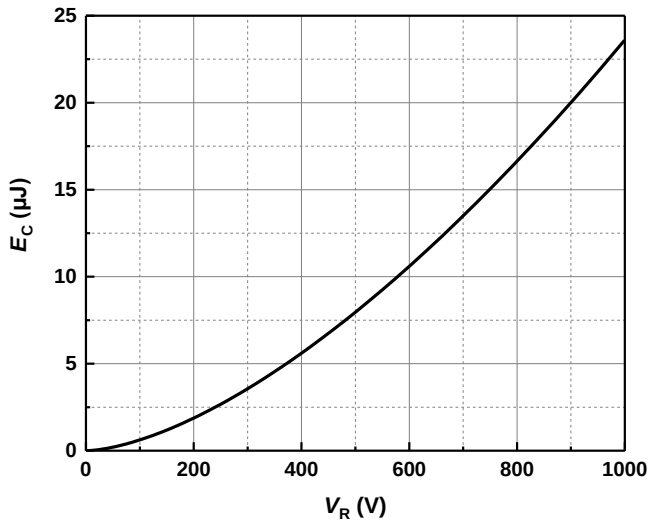


Figure 7. Capacitance stored energy

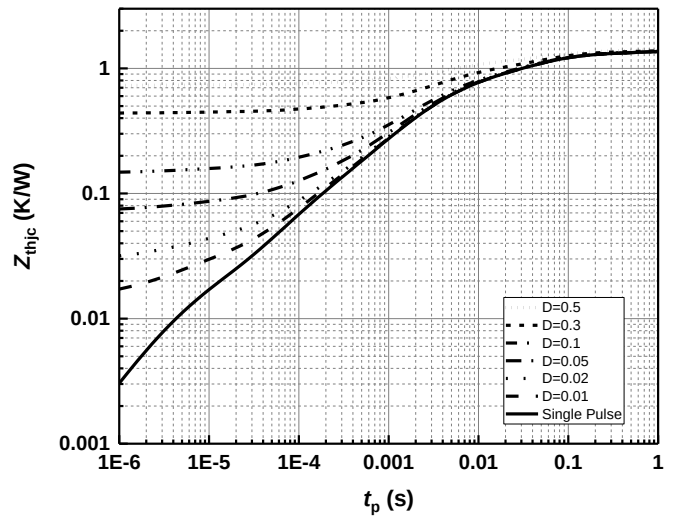
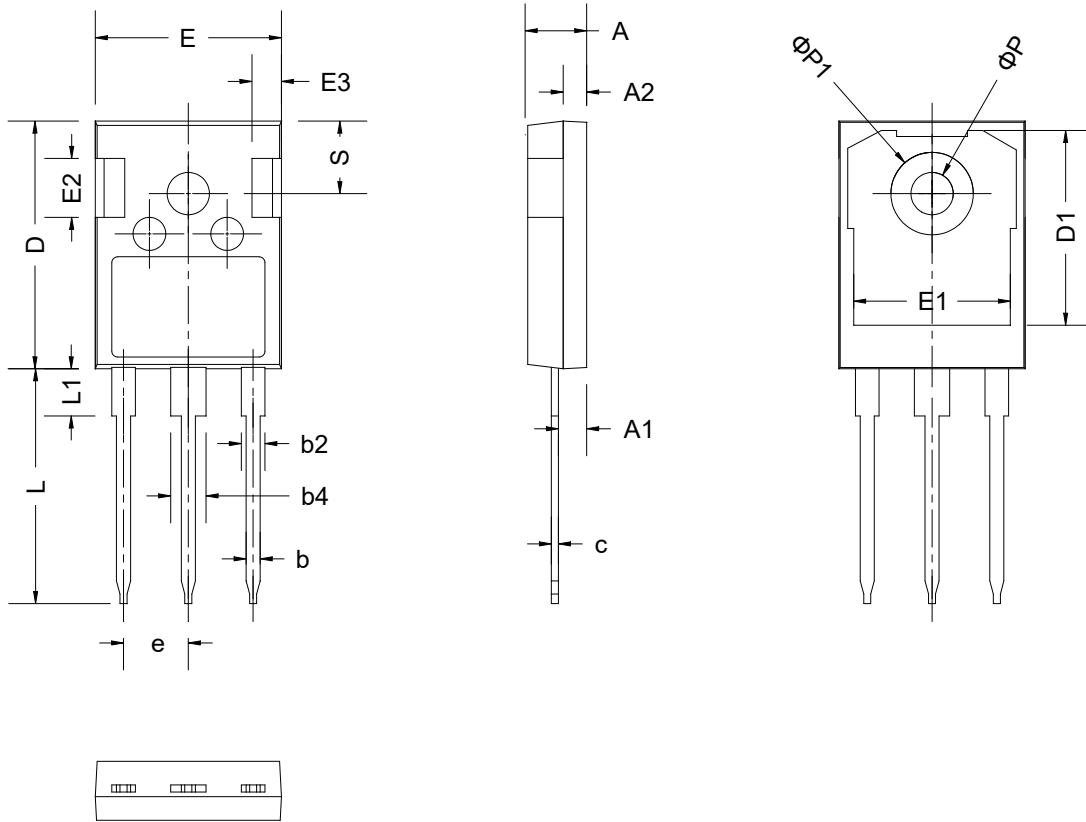


Figure 8. Max. transient thermal impedance, $Z_{thjc} = f(t)$, parameter: $D = t/T$

Package Dimensions



SYMBOL	mm		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44 BSC		
L	19.62	19.92	20.22
L1	-	-	4.30
φ P	3.40	3.60	3.80
φ P1	-	-	7.30
S	6.16 BSC		

Revision History

Document Version	Date of Release	Description of Changes
Rev. 1.0	2020-07-06	Release of the datasheet.
Rev. 1.1	2020-12-05	Characteristics updated.

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